

# RJH1CD5DPQ-E0

1200V - 20A - IGBT Application: Inverter

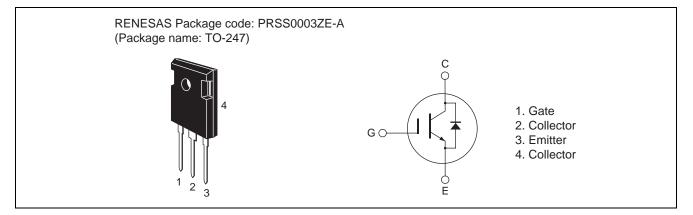
R07DS0517EJ0400 Rev.4.00 Jan 19, 2012

# Features

- Short circuit withstand time (5 µs typ.)
- Low collector to emitter saturation voltage  $V_{CE(sat)} = 2.0 \text{ V}$  typ. (at  $I_C = 20 \text{ A}$ ,  $V_{GE} = 15 \text{ V}$ ,  $Ta = 25^{\circ}\text{C}$ )
- Built-in fast recovery diode ( $t_{rr} = 200$  ns typ.) in one package
- Trench gate and thin wafer technology
- High speed switching

 $t_f = 100$  ns typ. (at  $V_{CC} = 600$  V,  $V_{GE} = 15$  V,  $I_C = 20$  A, Rg = 5  $\Omega$ ,  $Ta = 25^{\circ}C$ , inductive load)

## Outline



## Absolute Maximum Ratings

			(Ta = 25°C)
ltem	Symbol	Ratings	Unit
tage / diode reverse voltage	V <sub>CES</sub> / V <sub>R</sub>	1200	V
•	V <sub>GES</sub>	±30	V
Tc = 25°C	lc	40	А
Tc = 100°C	lc	20	А
	ic(peak) <sup>Note1</sup>	60	А
de forward current	I <sub>DF</sub>	20	А
de forward peak current	i <sub>DF</sub> (peak) Note1	60	А
	Pc <sup>Note2</sup>	260.4	W
al resistance (IGBT)	θj-c <sup>Note2</sup>	0.48	°C/W
	Tj	150	٥°
	Tstg	-55 to +150	٥°
	tage / diode reverse voltage $Tc = 25^{\circ}C$ $Tc = 100^{\circ}C$ de forward current de forward peak current	$\begin{tabular}{ c c c c c c } tage / diode reverse voltage & V_{CES} / V_R & V_{GES} & V_{GES} & V_{GES} & & V_{GES} & & & \\ \hline Tc = 25^\circ C & I_C & & & & \\ \hline Tc = 100^\circ C & I_C & & & & \\ \hline tc (peak)^{Note1} & & & & & \\ \hline de forward current & & & & & & & \\ \hline de forward peak current & & & & & & & \\ \hline de forward peak current & & & & & & & \\ \hline de forward peak current & & & & & & & \\ \hline de forward peak current & & & & & & & \\ \hline de forward peak current & & & & & & & \\ \hline de forward peak current & & & & & & & \\ \hline de forward peak current & & & & & & & \\ \hline de forward peak current & & & & & & & \\ \hline de forward peak current & & & & & & & \\ \hline de forward peak current & & & & & & & \\ \hline de forward peak current & & & & & & & & \\ \hline de forward peak current & & & & & & & & \\ \hline de forward peak current & & & & & & & & \\ \hline de forward peak current & & & & & & & & & \\ \hline de forward peak current & & & & & & & & \\ \hline de forward peak current & & & & & & & & \\ \hline de forward peak current & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & \\ \hline de forward peak current & & & & & & & & \\ \hline de forward peak current & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & & & & & \\ \hline de forward peak current & & & & & & & & & & & & & & & & & & &$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tc = 25°C



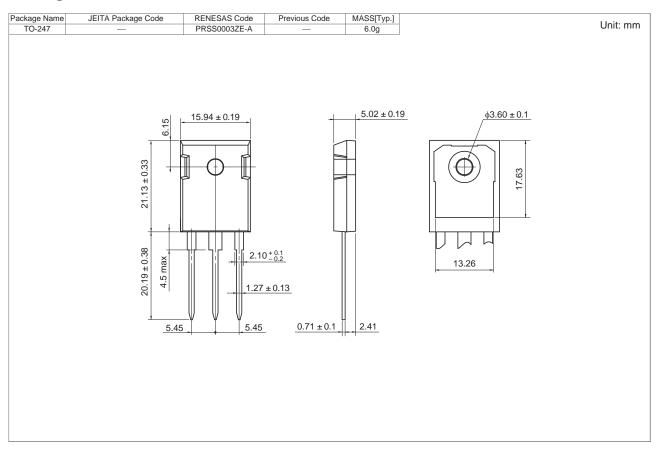
# **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current / Diode reverse current	I <sub>CES</sub> /I <sub>R</sub>		—	5	μΑ	$V_{CE} = 1200 V, V_{GE} = 0$
Gate to emitter leak current	I <sub>GES</sub>	_		±1	μA	$V_{GE} = \pm 30 \text{ V},  V_{CE} = 0$
Gate to emitter cutoff voltage	V <sub>GE(off)</sub>	4	_	8	V	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	_	2.0	_	V	$I_{C} = 20 \text{ A}, V_{GE} = 15 \text{ V}^{Note3}$
Input capacitance	Cies	_	1100	_	pF	V <sub>CE</sub> = 25 V
Output capacitance	Coes	_	40	_	pF	V <sub>GE</sub> = 0 f = 1 MHz
Reveres transfer capacitance	Cres	_	25	_	pF	
Switching time	t <sub>d(on)</sub>		40		ns	$V_{CC} = 600 \text{ V}, \text{ V}_{GE} = 15 \text{ V}$ $I_C = 20 \text{ A}$ $\text{Rg} = 5 \Omega$ Inductive load
	tr	_	15	_	ns	
	t <sub>d(off)</sub>	_	90		ns	
	t <sub>f</sub>	_	100	—	ns	
Short circuit withstand time	t <sub>sc</sub>	_	5		μS	$V_{CC} \leq 720 \text{ V}, \text{ V}_{GE} = 15 \text{ V}$
						$Tc \le 125^{\circ}C$
FRD forward voltage	VF	_	1.7		V	I <sub>F</sub> = 20 A <sup>Note3</sup>
FRD reverse recovery time	t <sub>rr</sub>	_	200	_	ns	I <sub>F</sub> = 20 A
						$di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 3. Pulse test.



### **Package Dimension**



## **Ordering Information**

Orderable Part Number	Quantity	Shipping Container
RJH1CD5DPQ-E0#T2	450 pcs	Box (Tube)



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